

### BD675A/677A/679A/681

# **Medium Power Linear and Switching Applications**

- Medium Power Darlington TR
- Complement to BD676A, BD678A, BD680A and BD682 respectively



## **NPN Epitaxial Silicon Transistor**

**Absolute Maximum Ratings** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter		Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	: BD675A	45	V	
		: BD677A	60	V	
		: BD679A	80	V	
		: BD681	100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	: BD675A	45	V	
		: BD677A	60	V	
		: BD679A	80	V	
		: BD681	100	V	
V <sub>EBO</sub>	Emitter-Base Voltage		5	V	
I <sub>C</sub>	Collector Current (DC)		4	А	
I <sub>CP</sub>	*Collector Current (Pulse)		6	А	
I <sub>B</sub>	Base Current		100	mA	
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)		40	W	
T <sub>J</sub>	Junction Temperature		150	°C	
T <sub>STG</sub>	Storage Temperature		- 65 ~ 150	°C	

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Param	eter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	*Collector-Emitter Sustain	ing Voltage : BD675A : BD677A : BD679A : BD681	I <sub>C</sub> = 50mA, I <sub>B</sub> = 0	45 60 80 100			V V V
I <sub>CBO</sub>	Collector-Base Voltage	: BD675A : BD677A : BD679A : BD681	$V_{CB} = 45V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 80V, I_{E} = 0$ $V_{CB} = 100V, V_{BE} = 0$			200 200 200 200	μΑ μΑ μΑ μΑ
I <sub>CEO</sub>	Collector Cut-off Current	: BD675A : BD677A : BD679A : BD681	$V_{CE} = 45V, V_{BE} = 0$ $V_{CE} = 60V, V_{BE} = 0$ $V_{CE} = 80V, V_{BE} = 0$ $V_{CE} = 100V, V_{BE} = 0$			500 500 500 500	μΑ μΑ μΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current		$V_{EB} = 5V, I_{C} = 0$			2	mA
h <sub>FE</sub>	* DC Current Gain	: BD675A/677A/679A : BD681	$V_{CE} = 3V, I_{C} = 2A$ $V_{CE} = 3V, I_{C} = 1.5A$	750 750			
V <sub>CE</sub> (sat)	* Collector-Emitter Satura	tion Voltage : BD675A/677A/679A : BD681	I <sub>C</sub> = 2A, I <sub>B</sub> = 40mA I <sub>C</sub> = 1.5A, I <sub>B</sub> = 30mA			2.8 2.5	V V
V <sub>BE</sub> (on)	* Base-Emitter ON Voltage	e : BD675A/677A/679A : BD681	$V_{CE} = 3V, I_{C} = 2A$ $V_{CF} = 3V, I_{C} = 1.5A$			2.5 2.5	V V

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# **Typical Characteristics**

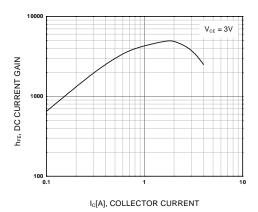


Figure 1. DC current Gain

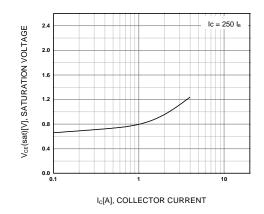


Figure 2. Collector-Emitter Saturation Voltage

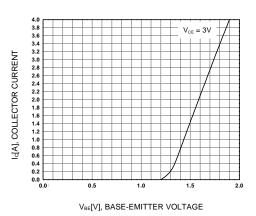


Figure 3. Base-Emitter On Voltage

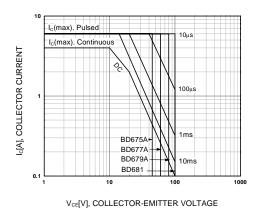


Figure 4. Safe Operating Area

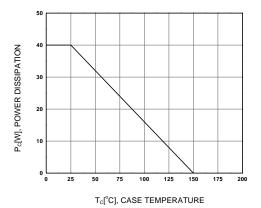
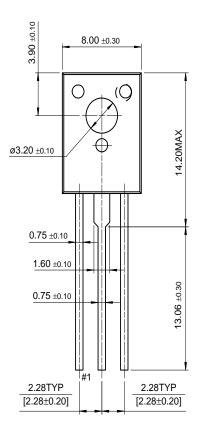


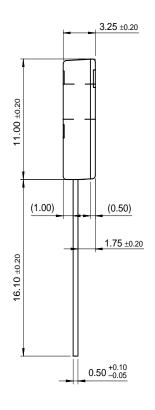
Figure 5. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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